

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>(PTO-1449)</b>		ATTY. DOCKET NO. <b>57810-084</b>		SERIAL NO. <b>Divisional of Appl No. 10/084,050</b>	
		APPLICANT <b>Nobuhiko HAYASHI, et al.</b>			
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U.S. PATENT DOCUMENTS					
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<del>De</del>     		US 6,015,979	1/18/2000	Sugiura et al.	
		US 6,051,849	4/16/2000	Davis et al.	
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
<del>De</del>     		2000-164989	6/16/2000			Yes	No
		2000-269144	9/29/2000			Japan (w/ English Abstract)	
		2000-21789	1/21/2000			Japan (w/ English Abstract)	
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<del>De</del>    		S. Nakamura et al., "Long lifetime violet InGaN/GaN/AlGaIn-based semiconductor lasers", Journal of Oyo Denshi Bussai Bunkakai, Vol. 4, (1998), pp. 53-58 and 210-215.
		Akira Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L899-L902.
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EXAMINER <span style="font-size: 1.5em; margin-left: 50px;">De</span>	DATE CONSIDERED <span style="font-size: 1.5em; margin-left: 50px;">12/2005</span>
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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